

2SD1135

Silicon NPN Triple Diffused

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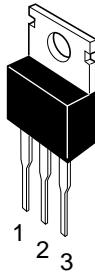
ADE-208-906 (Z)
1st. Edition
Sep. 2000

Application

Low frequency power amplifier complementary pair with 2SB859

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	100	V
Collector to emitter voltage	V_{CEO}	80	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_{C}	4	A
Collector peak current	$I_{\text{C(peak)}}$	8	A
Collector power dissipation	P_{C}^{*1}	40	W
Junction temperature	T_{j}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-45 to +150	$^\circ\text{C}$

Note: 1. Value at $T_{\text{c}} = 25^\circ\text{C}$.

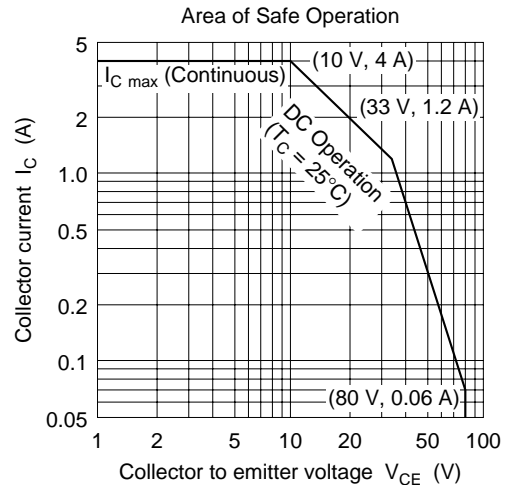
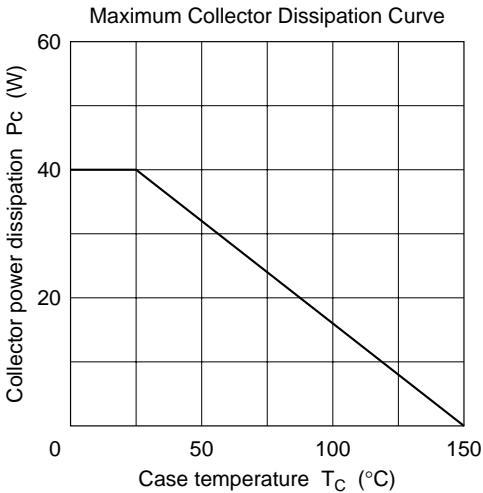
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	80	—	—	V	$I_C = 50 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10 \text{ }\mu\text{A}, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.1	mA	$V_{CB} = 80 \text{ V}, I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	200		$V_{CE} = 5 \text{ V}, I_C = 1 \text{ A}^{*2}$
	h_{FE2}	35	—	—		$V_{CE} = 5 \text{ V}, I_C = 0.1 \text{ A}^{*2}$
Base to emitter voltage	V_{BE}	—	—	1.5	V	$V_{CE} = 5 \text{ V}, I_C = 1 \text{ A}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	2	V	$I_C = 2 \text{ A}, I_B = 0.2 \text{ A}^{*2}$
Gain bandwidth product	f_T	—	10	—	MHz	$V_{CE} = 5 \text{ V}, I_C = 0.5 \text{ A}^{*2}$
Collector output capacitance	Cob	—	40	—	pF	$V_{CB} = 20 \text{ V}, I_E = 0, f = 1 \text{ MHz}$

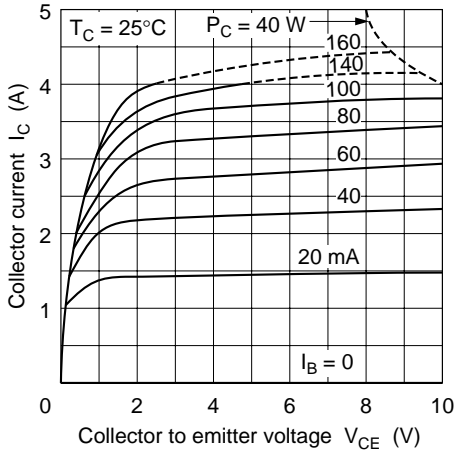
Notes: 1. The 2SD1135 is grouped by h_{FE1} as follows.

2. Pulse test.

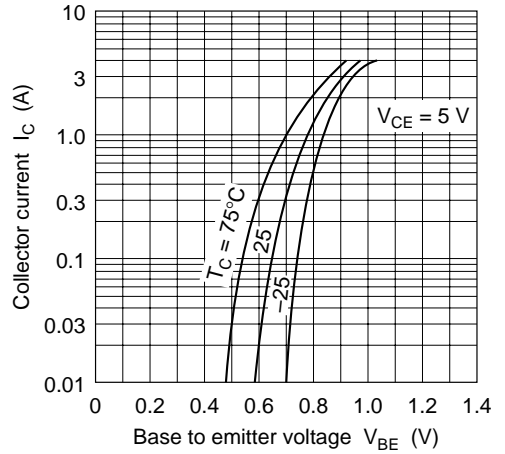
B	C
60 to 120	100 to 200



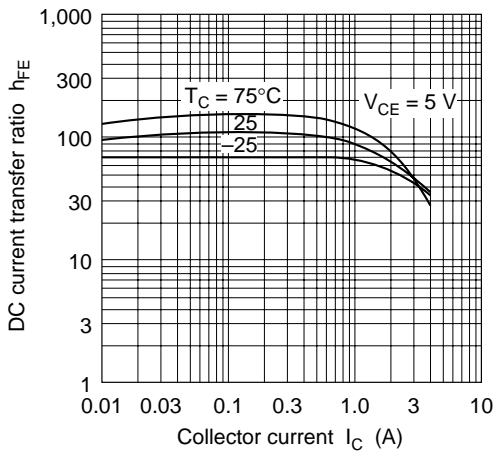
Typical Output Characteristics



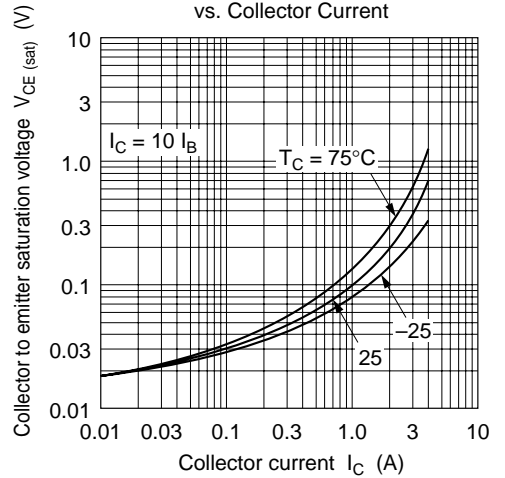
Typical Transfer Characteristics



DC Current Transfer Ratio vs. Collector Current

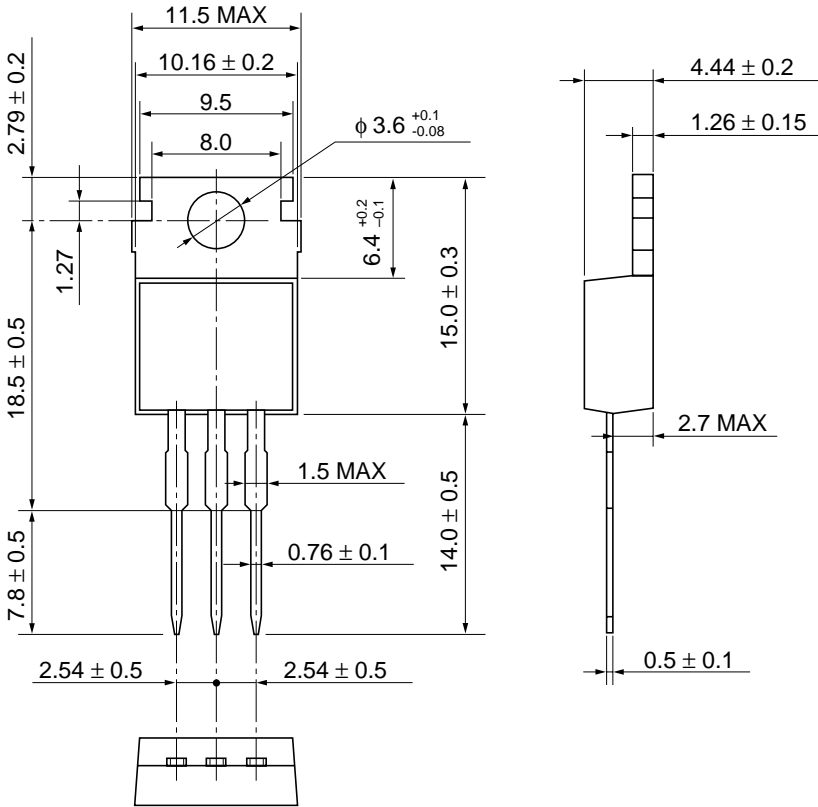


Collector to Emitter Saturation Voltage vs. Collector Current



Package Dimensions

Unit: mm



Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	1.8 g

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